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# SN74GTLPH1655 16-BIT LVTTL-TO-GTLP ADJUSTABLE-EDGE-RATE UNIVERSAL BUS TRANSCEIVER

SCES294C-OCTOBER 1999-REVISED MAY 2005

#### **FEATURES**

- Member of Texas Instruments' Widebus™
   Family
- UBT<sup>™</sup> Transceiver Combines D-Type Latches and D-Type Flip-Flops for Operation in Transparent, Latched, or Clocked Modes
- TI-OPC<sup>™</sup> Circuitry Limits Ringing on Unevenly Loaded Backplanes
- OEC<sup>™</sup> Circuitry Improves Signal Integrity and Reduces Electromagnetic Interference
- Bidirectional Interface Between GTLP Signal Levels and LVTTL Logic Levels
- Partitioned as Two 8-Bit Transceivers With Individual Latch Timing and Output Control, but With a Common Clock
- LVTTL Interfaces Are 5-V Tolerant
- High-Drive GTLP Outputs (100 mA)
- LVTTL Outputs (–24 mA/24 mA)
- Variable Edge-Rate Control (ERC) Input Selects GTLP Rise and Fall Times for Optimal Data-Transfer Rate and Signal Integrity in Distributed Loads
- I<sub>off</sub>, Power-Up 3-State, and BIAS V<sub>CC</sub> Support Live Insertion
- Bus Hold on A-Port Data Inputs
- Distributed V<sub>CC</sub> and GND Pins Minimize High-Speed Switching Noise
- Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II
- ESD Protection Exceeds JESD 22
  - 2000-V Human-Body Model (A114-A)
  - 200-V Machine Model (A115-A)
  - 1000-V Charged-Device Model (C101)

#### DGG PACKAGE (TOP VIEW)

	_	$\overline{}$	$\neg$	
1 <del>OEAB</del> [	1	$\cup$	64	CLK
1 <del>OEBA</del> [	2		63	1LEAB
v <sub>cc</sub> [	3		62	1LEBA
1A1 [			61	ERC
GND [	5		60	GND
1A2 [	6		59	1B1
1A3 [	7		58	1B2
GND [	8		57	GND
1A4 [	9		56	1B3
GND [	10		55	1B4
1A5 [			54	1B5
GND [	12			GND
1A6 [	13		52	1B6
_	14			1B7
v <sub>cc</sub> [	15		50	$V_{CC}$
1A8 [			49	1B8
2A1 [	17		48	2B1
GND [			47	GND
2A2 [	19			2B2
2A3 [	20			2B3
GND [				GND
2A4 [	22			2B4
2A5 [	23		42	2B5
GND [	24		41	$V_{REF}$
2A6 [	25		40	2B6
GND [	26			GND
2A7 [	27			
V <sub>CC</sub> [	28			2B8
2A8 [	1			$BIAS\;V_{CC}$
GND [	1			2LEAB
2 <del>OEAB</del>	31		34	2LEBA
2OEBA	32		33	ŌĒ

### **DESCRIPTION**

The SN74GTLPH1655 is a high-drive, 16-bit UBT<sup>TM</sup> transceiver that provides LVTTL-to-GTLP and GTLP-to-LVTTL signal-level translation. It is partitioned as two 8-bit transceivers and allows for transparent, latched, and clocked modes of data transfer. The device provides a high-speed interface between cards operating at LVTTL logic levels and a backplane operating at GTLP signal levels. High-speed (about three times faster than standard LVTTL or TTL) backplane operation is a direct result of GTLP's reduced output swing (<1 V), reduced input threshold levels, improved differential input, OEC<sup>TM</sup> circuitry, and TI-OPC<sup>TM</sup> circuitry. Improved GTLP OEC and TI-OPC circuits minimize bus-settling time and have been designed and tested using several backplane models. The high drive allows incident-wave switching in heavily loaded backplanes with equivalent load impedance down to 11 Ω.



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### **DESCRIPTION (CONTINUED)**

GTLP is the Texas Instruments (TI<sup>TM</sup>) derivative of the Gunning Transceiver Logic (GTL) JEDEC standard JESD 8-3. The ac specification of the SN74GTLPH1655 is given only at the preferred higher noise-margin GTLP, but the user has the flexibility of using this device at either GTL ( $V_{TT} = 1.2 \text{ V}$  and  $V_{REF} = 0.8 \text{ V}$ ) or GTLP ( $V_{TT} = 1.5 \text{ V}$  and  $V_{REF} = 1 \text{ V}$ ) signal levels.

Normally, the B port operates at GTLP signal levels. The A-port and control inputs operate at LVTTL logic levels, but are 5-V tolerant and are compatible with TTL and 5-V CMOS inputs.  $V_{REF}$  is the B-port differential input reference voltage.

This device is fully specified for live-insertion applications using  $I_{\text{off}}$ , power-up 3-state, and BIAS  $V_{\text{CC}}$ . The  $I_{\text{off}}$  circuitry disables the outputs, preventing damaging current backflow through the device when it is powered down. The power-up 3-state circuitry places the outputs in the high-impedance state during power up and power down, which prevents driver conflict. The BIAS  $V_{\text{CC}}$  circuitry precharges and preconditions the B-port input/output connections, preventing disturbance of active data on the backplane during card insertion or removal, and permits true live-insertion capability.

This GTLP device features TI-OPC circuitry, which actively limits overshoot caused by improperly terminated backplanes, unevenly distributed cards, or empty slots during low-to-high signal transitions. This improves signal integrity, which allows adequate noise margin to be maintained at higher frequencies.

High-drive GTLP backplane interface devices feature adjustable edge-rate control (ERC). Changing the ERC input voltage between GND and  $V_{CC}$  adjusts the B-port output rise and fall times. This allows the designer to optimize system data-transfer rate and signal integrity to the backplane load.

Active bus-hold circuitry holds unused or undriven LVTTL data inputs at a valid logic state. Use of pullup or pulldown resistors with the bus-hold circuitry is not recommended.

When  $V_{CC}$  is between 0 and 1.5 V, the device is in the high-impedance state during power up or power down. However, to ensure the high-impedance state above 1.5 V, the output-enable ( $\overline{OE}$ ) input should be tied to  $V_{CC}$  through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

#### ORDERING INFORMATION

T <sub>A</sub>	PACKAGE <sup>(1)</sup>		ORDERABLE PART NUMBER	TOP-SIDE MARKING	
-40°C to 85°C	TSSOP - DGG	Tape and reel	SN74GTLPH1655DGGR	GTLPH1655	

<sup>(1)</sup> Package drawings, standard packing quantities, thermal data, symbolization, and PCB design guidelines are available at www.ti.com/sc/package.

#### **FUNCTIONAL DESCRIPTION**

The SN74GTLPH1655 is a high-drive (100 mA), 16-bit UBT transceiver containing D-type latches and D-type flip-flops for data-path operation in transparent, latched, or clocked modes. The device is uniquely partitioned as two 8-bit transceivers with individual latch timing and output signals and a common clock for both transceiver words. It can replace any of the functions shown in Table 1. Data polarity is noninverting.

Table 1. SN74GTLPH1655 UBT Transceiver Replacement Functions

FUNCTION	8 BIT	9 BIT	10 BIT	16 BIT
Transceiver	'245, '623, '645	'863	'861	'16245, '16623
Buffer/driver	'241, '244, '541		'827	'16241, '16244, '16541
Latched transceiver	'543			'16543
Latch	'373, '573	'843	'841	'16373
Registered transceiver	'646, '652			'16646, '16652
Flip-flop	'374, '574		'821	'16374
SN740	GTLPH1655 UBT transcei	ver replaces a	all above fur	ections



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## **FUNCTIONAL DESCRIPTION (CONTINUED)**

Data flow for each word is determined by the respective latch enables (xLEAB and xLEBA), output enables (xOEAB and xOEBA), and clock (CLK). The output enables (1OEAB, 1OEBA, 2OEAB, and 2OEBA) control byte 1 and byte 2 data for the A-to-B and B-to-A directions, respectively. Note that CLK is common to both directions and both 8-bit words. OE also is common and disables all I/O ports simultaneously.

For A-to-B data flow, the devices operate in the transparent mode when LEAB is high. When LEAB transitions low, the A data is latched independent of CLK high or low. If LEAB is low, the A data is registered on the CLK low-to-high transition. When  $\overline{OEAB}$  is low, the outputs are active. With  $\overline{OEAB}$  high, the outputs are in the high-impedance state.

The data flow for the B-to-A direction is identical, except OEBA, LEBA, and CLK are used.

#### **FUNCTION TABLES**

#### **FUNCTION**(1)

	INPUTS			OUTPUT	MODE
OEAB	LEAB	CLK	Α	В	WIODE
Н	Χ	Χ	Χ	Z	Isolation
L	L	Н	Х	B <sub>0</sub> <sup>(2)</sup>	Latabad atarage of A data
L	L	L	Χ	B <sub>0</sub> <sup>(3)</sup>	Latched storage of A data
L	Н	Χ	L	L	True transparent
L	Н	Χ	Н	Н	True transparent
L	L	1	L	L	Clasked starage of A data
L	L	1	Н	Н	Clocked storage of A data

- (1) A-to-B data flow is shown. B-to-A flow is similar, but uses <del>OEBA</del>, LEBA, and CLK. The condition when <del>OEAB</del> and <del>OEBA</del> are both low at the same time is not recommended.
- (2) Output level before the indicated steady-state input conditions were established, provided that CLK was high before LEAB went low
- (3) Output level before the indicated steady-state input conditions were established

### **OUTPUT ENABLE**

	INPUTS	OUTI	PUTS	
ŌĒ	OEAB	OEBA	A PORT	B PORT
L	L	L	Active	Active <sup>(1)</sup>
L	L	Н	Z	Active
L	Н	L	Active	Z
L	Н	Н	Z	Z
Н	X	X	Z	Z

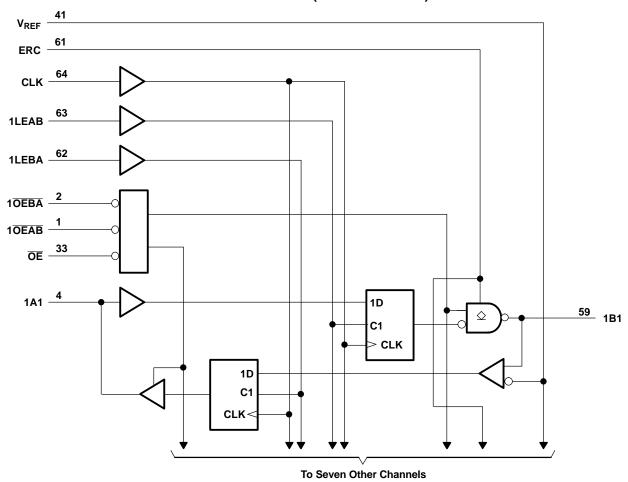
(1) This condition is not recommended.

#### **B-PORT EDGE-RATE CONTROL (ERC)**

INPU'	T ERC	OUTPUT
LOGIC LEVEL	NOMINAL VOLTAGE	B-PORT EDGE RATE
Н	V <sub>CC</sub>	Slow
L	GND	Fast



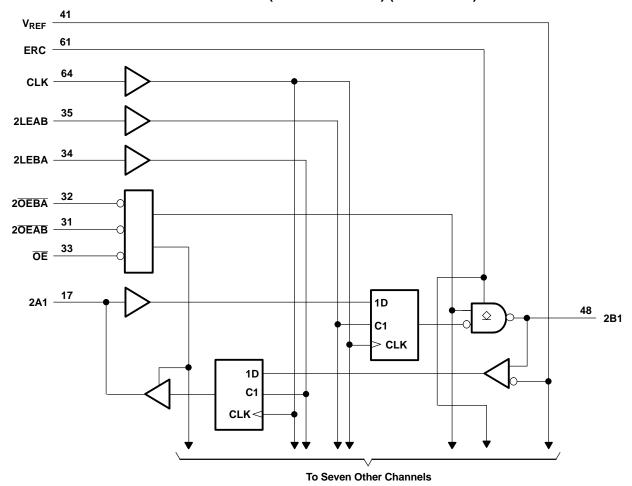
# **LOGIC DIAGRAM (POSITIVE LOGIC)**





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# LOGIC DIAGRAM (POSITIVE LOGIC) (CONTINUED)



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# Absolute Maximum Ratings<sup>(1)</sup>

over operating free-air temperature range (unless otherwise noted)

			MIN	MAX	UNIT
$V_{CC}$ BIAS $V_{CC}$	Supply voltage range			4.6	V
V	Input voltage range <sup>(2)</sup>	A port, ERC, and control inputs	-0.5	7	V
VI	input voltage range (-)	B port and V <sub>REF</sub>	-0.5	4.6	V
V	Voltage range applied to any output	A port	-0.5	7	V
Vo	in the high-impedance or power-off state <sup>(2)</sup>	B port	-0.5	4.6	V
	Current into any output in the law state	A port		48	A
Io	Current into any output in the low state	B port		200	mA
Io	Current into any A-port output in the high state (3)			48	mA
	Continuous current through each V <sub>CC</sub> or GND			±100	mA
I <sub>IK</sub>	Input clamp current	V <sub>I</sub> < 0		-50	mA
I <sub>OK</sub>	Output clamp current	V <sub>O</sub> < 0		-50	mA
$\theta_{JA}$	Package thermal impedance <sup>(4)</sup>			55	°C/W
T <sub>stg</sub>	Storage temperature range		-65	150	°C

<sup>(1)</sup> Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

(3) This current flows only when the output is in the high state and V<sub>O</sub> > V<sub>CC</sub>.
 (4) The package thermal impedance is calculated in accordance with JESD 51-7.



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# Recommended Operating Conditions (1)(2)(3)(4)

			MIN	NOM	MAX	UNIT	
V <sub>CC</sub> , BIAS V <sub>CC</sub>	Supply voltage		3.15	3.3	3.45	V	
W	Termination voltage	GTL	1.14	1.2	1.26	V	
$V_{TT}$	Termination voltage	GTLP	1.35	1.5	1.65	V	
\/	Peferance voltage	GTL	0.74	0.8	0.87	V	
$V_{REF}$	Reference voltage	GTLP	0.87	1	1.1	V	
W	Input voltage	B port			$V_{TT}$	V	
V <sub>I</sub>	Input voltage	Except B port		V <sub>CC</sub>	5.5	V	
		B port	V <sub>REF</sub> + 0.05				
$V_{IH}$	High-level input voltage	ERC	V <sub>CC</sub> - 0.6	V <sub>CC</sub>	5.5	V	
		Except B port and ERC	2				
		B port			V <sub>REF</sub> - 0.05		
$V_{IL}$	Low-level input voltage	ERC		GND	0.6	V	
		Except B port and ERC			0.8		
I <sub>IK</sub>	Input clamp current				-18	mA	
I <sub>OH</sub>	High-level output current	A port			-24	mA	
	I am land antant amount	A port			24	A	
l <sub>OL</sub>	Low-level output current	B port			100	mA	
Δt/Δν	Input transition rise or fall rate	Outputs enabled			10	ns/V	
$\Delta t/\Delta V_{CC}$	Power-up ramp rate		20			μs/V	
T <sub>A</sub>	Operating free-air temperature		-40		85	°C	

(1) All unused control and B-port inputs of the device must be held at V<sub>CC</sub> or GND to ensure proper device operation. Refer to the TI

application report, Implications of Slow or Floating CMOS Inputs, literature number SCBA004. Proper connection sequence for use of the B-port I/O precharge feature is GND and BIAS  $V_{CC} = 3.3 \text{ V}$  first, I/O second, and  $V_{CC} = 3.3 \text{ V}$  last, because the BIAS  $V_{CC}$  precharge circuitry is disabled when any  $V_{CC}$  pin is connected. The control and  $V_{REF}$  inputs can be connected any onnected during the I/O stage. If B-port precharge is not required, any connection sequence is acceptable, but generally, GND is connected first.

 $V_{TT}$  and  $R_{TT}$  can be adjusted to accommodate backplane impedances if the dc recommended  $I_{OL}$  ratings are not exceeded.  $V_{REF}$  can be adjusted to optimize noise margins, but normally is two-thirds  $V_{TT}$ . TI-OPC circuitry is enabled in the A-to-B direction and is activated when  $V_{TT} > 0.7$  V above  $V_{REF}$ . If operated in the A-to-B direction,  $V_{REF}$  should be set to within 0.6 V of  $V_{TT}$  to minimize current

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#### **Electrical Characteristics**

over recommended operating free-air temperature range for GTLP (unless otherwise noted)

P	ARAMETER	TEST CONDITIONS		MIN	TYP <sup>(1)</sup>	MAX	UNIT
V <sub>IK</sub>		V <sub>CC</sub> = 3.15 V,	I <sub>I</sub> = -18 mA			-1.2	V
		V <sub>CC</sub> = 3.15 V to 3.45 V,	$I_{OH} = -100 \ \mu A$	V <sub>CC</sub> - 0.2			
$V_{OH}$	OH A port	V 0.45.V	I <sub>OH</sub> = -12 mA	2.4			V
		V <sub>CC</sub> = 3.15 V	$I_{OH} = -24 \text{ mA}$	2		-1.2  0.2  0.4  0.5  0.2  0.4  0.55  ±10  10  -10  40  40  40  1.5  5  6.5  7.5	
		$V_{CC} = 3.15 \text{ V to } 3.45 \text{ V},$	$I_{OL} = 100 \mu A$			0.2	
	A port	V <sub>CC</sub> = 3.15 V	$I_{OL} = 12 \text{ mA}$			0.4	
V		V <sub>CC</sub> = 3.15 V	$I_{OL} = 24 \text{ mA}$			0.5	V
$V_{OL}$	OL		$I_{OL} = 10 \text{ mA}$			0.2	V
	B port	V <sub>CC</sub> = 3.15 V	$I_{OL} = 64 \text{ mA}$			0.4	
			I <sub>OL</sub> = 100 mA			0.55	
I <sub>I</sub>	Control inputs	$V_{CC} = 3.45 \text{ V},$	$V_{I} = 0 \text{ or } 5.5 \text{ V}$			±10	μΑ
I <sub>OZH</sub> <sup>(2)</sup>	A port	V <sub>CC</sub> = 3.45 V	$V_O = V_{CC}$			10	μΑ
'OZH` ′	B port	V <sub>CC</sub> = 3.43 V	V <sub>O</sub> = 1.5 V			10	μΑ
I <sub>OZL</sub> <sup>(2)</sup>	A and B ports	$V_{CC} = 3.45 \text{ V},$	$V_O = GND$			-10	μΑ
I <sub>BHL</sub> <sup>(3)</sup>	A port	$V_{CC} = 3.15 \text{ V},$	$V_{I} = 0.8 \ V$	75			μΑ
I <sub>BHH</sub> <sup>(4)</sup>	A port	$V_{CC} = 3.15 \text{ V},$	$V_I = 2 V$	-75			μΑ
I <sub>BHLO</sub> <sup>(5)</sup>	A port	$V_{CC} = 3.45 \text{ V},$	$V_I = 0$ to $V_{CC}$	500			μΑ
I <sub>BHHO</sub> <sup>(6)</sup>	A port	$V_{CC} = 3.45 \text{ V},$	$V_I = 0$ to $V_{CC}$	-500			μΑ
		$V_{CC} = 3.45 \text{ V}, I_{C} = 0,$	Outputs high			40	
$I_{CC}$	A or B port	$V_{I}$ (A-port or control input) = $V_{CC}$ or GND,	Outputs low			40	mA
		$V_{I}$ (B port) = $V_{TT}$ or GND	Outputs disabled			40	
$\Delta I_{CC}^{(7)}$		$V_{CC}$ = 3.45 V, One A-port or control input at Other A-port or control inputs at $V_{CC}$ or GNE				1.5	mA
C <sub>i</sub>	Control inputs	V <sub>I</sub> = 3.15 V or 0			4.5	6.5	pF
C.	A port	V <sub>O</sub> = 3.15 V or 0			6.5	7.5	pF
C <sub>io</sub>	B port	V <sub>O</sub> = 1.5 V or 0			8.5	10.5	рг

- All typical values are at V<sub>CC</sub> = 3.3 V, T<sub>A</sub> = 25°C.
   For I/O ports, the parameters I<sub>OZH</sub> and I<sub>OZL</sub> include the input leakage current.
   The bus-hold circuit can sink at least the minimum low sustaining current at V<sub>IL</sub>max. I<sub>BHL</sub> should be measured after lowering V<sub>IN</sub> to GND and then raising it to  $V_{\text{IL}}$ max.
- The bus-hold circuit can source at least the minimum high sustaining current at V<sub>IH</sub>min. I<sub>BHH</sub> should be measured after raising V<sub>IN</sub> to V<sub>CC</sub> and then lowering it to  $V_{IH}min$ .
- An external driver must source at least  $I_{BHLO}$  to switch this node from low to high. An external driver must sink at least  $I_{BHHO}$  to switch this node from high to low.
- This is the increase in supply current for each input that is at the specified TTL voltage level, rather than V<sub>CC</sub> or GND.

### **Hot-Insertion Specifications for A Port**

over operating free-air temperature range

PARAMETER		TEST CONDITION	IS	MIN	MAX	UNIT
l <sub>off</sub>	$V_{CC} = 0$ ,	BIAS $V_{CC} = 0$ ,	$V_I$ or $V_O = 0$ to 5.5 V		10	μΑ
I <sub>OZPU</sub>	$V_{CC} = 0 \text{ to } 1.5 \text{ V},$	$V_0 = 0.5 V \text{ to } 3 V,$	<del>OE</del> = 0		±30	μΑ
I <sub>OZPD</sub>	$V_{CC} = 1.5 \text{ V to } 0,$	$V_0 = 0.5 \text{ V to 3 V},$	$\overline{OE} = 0$		±30	μΑ



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## **Live-Insertion Specifications for B Port**

over operating free-air temperature range

PARAMETER		TEST CONDITIONS		MIN	MAX	TINU
I <sub>off</sub>	$V_{CC} = 0$ ,	BIAS $V_{CC} = 0$ ,	$V_I$ or $V_O = 0$ to 1.5 V		10	μΑ
I <sub>OZPU</sub>	$V_{CC} = 0 \text{ to } 1.5 \text{ V},$	BIAS $V_{CC} = 0$ ,	$V_O = 0.5 \text{ V to } 1.5 \text{ V}, \overline{OE} = 0$		±30	μΑ
I <sub>OZPD</sub>	$V_{CC} = 1.5 \text{ V to } 0,$	BIAS $V_{CC} = 0$ ,	$V_O = 0.5 \text{ V to } 1.5 \text{ V}, \overline{OE} = 0$		±30	μΑ
I (DIACA)	$V_{CC} = 0 \text{ to } 3.15 \text{ V}$	PIAC V = 2.15 V to 2.45 V	$V_{O}$ (B port) = 0 to 1.5 V		5	mA
I <sub>CC</sub> (BIAS V <sub>CC</sub> )	$V_{CC} = 3.15 \text{ V to } 3.45 \text{ V}$	BIAS $V_{CC} = 3.15 \text{ V to } 3.45 \text{ V},$	v <sub>O</sub> (В роп) = 0 to 1.5 v		10	μΑ
Vo	$V_{CC} = 0$ ,	BIAS $V_{CC} = 3.3 \text{ V}$	I <sub>O</sub> = 0	0.95	1.05	٧
Io	V <sub>CC</sub> = 0,	BIAS $V_{CC} = 3.15 \text{ V to } 3.45 \text{ V},$	V <sub>O</sub> (B port) = 0.6 V	-1		μΑ

### **Timing Requirements**

over recommended ranges of supply voltage and operating free-air temperature,  $V_{TT}$  = 1.5 V and  $V_{REF}$  = 1 V for GTLP (unless otherwise noted)

			MIN	MAX	UNIT
f <sub>clock</sub>	Clock frequency			175	MHz
+	Dulas direction	LEAB or LEBA high	3		
t <sub>w</sub>	Pulse duration	CLK high or low	3		ns
		A before CLK	3		
		B before CLK	3		
t <sub>su</sub>	Setup time	A before LEAB↓, CLK = don't care	2.5		ns
		B before LEBA↓, CLK = don't care	175 3 3 3 3 2.5 2.5 0.5 0.5 0.5		
		A after CLK	0.5		
	B after CLK	0.5			
t <sub>h</sub>	noid time	A after LEAB↓, CLK = don't care	0.5		ns
	Pulse duration  Setup time  Hold time	B after LEBA↓, CLK = don't care	0.5		

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### **Switching Characteristics**

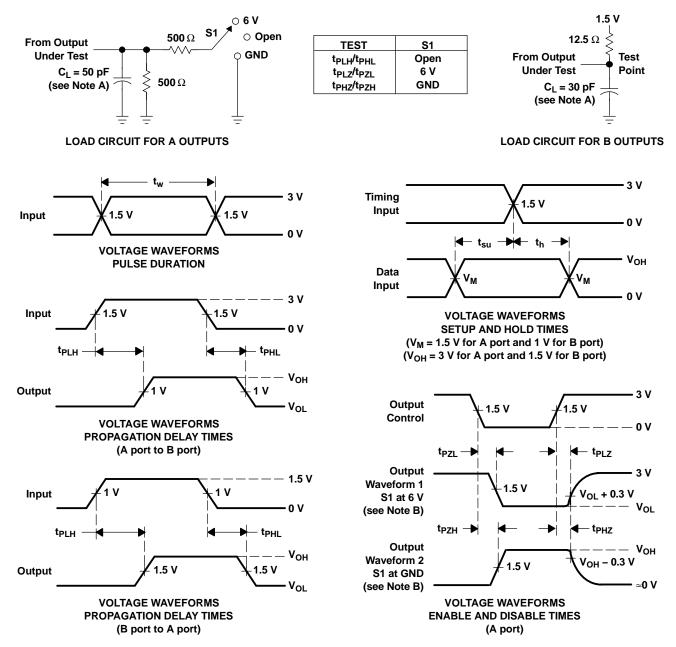
over recommended ranges of supply voltage and operating free-air temperature,  $V_{TT}$  = 1.5 V and  $V_{REF}$  = 1 V for GTLP (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	EDGE RATE(1)	MIN	TYP <sup>(2)</sup> MAX	UNIT	
f <sub>max</sub>				175		MHz	
t <sub>PLH</sub>	Α	В	Slow	3.5	7.7	ns	
t <sub>PHL</sub>		Б	Slow	2.4	6.3	113	
t <sub>PLH</sub>	А	В	Fast	2	6.3	ns	
t <sub>PHL</sub>	^	Б	i asi	2	5.9	113	
t <sub>PLH</sub>	LEAB	В	Slow	3.5	7.8	ns	
t <sub>PHL</sub>	LLAD	Б	Slow	2.7	6.4	113	
t <sub>PLH</sub>	LEAB	В	Fast	2	6.4	ns	
t <sub>PHL</sub>	LLAD	Б	i asi	2	6	113	
t <sub>PLH</sub>	CLK	В	Slow	4.7	8	ns	
t <sub>PHL</sub>	CLK	В	Slow	2.7	6.4	115	
t <sub>PLH</sub>	CLK	В	Fast	3.6	6.8	no	
t <sub>PHL</sub>	CLK	Б	rasi	2	6.1	ns	
t <sub>en</sub>	ŌĒ	В	Slow	3.5	7.3	20	
t <sub>dis</sub>	OE	Б	Slow	3.5	7	ns	
t <sub>en</sub>	ŌĒ	В	Fast	2	6	no	
t <sub>dis</sub>	OE	Б	rasi	2	6.6	ns	
t <sub>en</sub>	<del>OEAB</del>	В	Slow	3.5	7.4	no	
t <sub>dis</sub>	OEAB	Б	Slow	3.5	7	ns	
t <sub>en</sub>	<del>OEAB</del>	В	Fast	2	6.1	no	
t <sub>dis</sub>	UEAB	Б	rasi	2	6.3	ns	
4	Pico timo. P outr	outs (20% to 80%)	Slow		2.6	no	
t <sub>r</sub>	Kise time, b outp	outs (20% to 60%)	Fast		ns		
	Fall time Doute	uto (000/ to 200/)	Slow				
t <sub>f</sub>	raii time, b outp	uts (80% to 20%)	Fast	2.2		ns	
t <sub>PLH</sub>	В	А		1.5	5.5	20	
t <sub>PHL</sub>	В	A		1.5	5.5	ns	
t <sub>PLH</sub>	LEBA	А		1.3	5.2	20	
t <sub>PHL</sub>	LEDA	A		1	5	ns	
t <sub>PLH</sub>	CLK	^		1.2	6.3		
t <sub>PHL</sub>	CLK	А		1	5	ns	
t <sub>en</sub>	ŌĒ	۸		1.5	5.6		
t <sub>dis</sub>	OE.	Α		1.5	6.1	ns	
t <sub>en</sub>	<del></del> OEBA	^		1.2	5.4	20	
t <sub>dis</sub>	OEBA	Α		2	6.1	ns	

<sup>(1)</sup> Slow (ERC =  $V_{CC}$ ) and Fast (ERC = GND) (2) All typical values are at  $V_{CC}$  = 3.3 V,  $T_A$  = 25°C.

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#### PARAMETER MEASUREMENT INFORMATION



NOTES: A.  $C_L$  includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR  $\approx$  10 MHz,  $Z_O = 50~\Omega$ ,  $t_r \approx 2$  ns,  $t_f \approx 2$  ns.
- D. The outputs are measured one at a time, with one transition per measurement.

Figure 1. Load Circuits and Voltage Waveforms



#### DISTRIBUTED-LOAD BACKPLANE SWITCHING CHARACTERISTICS

The preceding switching characteristics table shows the switching characteristics of the device into a lumped load (Figure 1). However, the designer's backplane application probably is a distributed load. The physical representation is shown in Figure 2. This backplane, or distributed load, can be approximated closely to a resistor inductance capacitance (RLC) circuit, as shown in Figure 3. This device has been designed for optimum performance in this RLC circuit. The following switching characteristics table shows the switching characteristics of the device into the RLC load, to help the designer better understand the performance of the GTLP device in this typical backplane. See www.ti.com/sc/gtlp for more information.

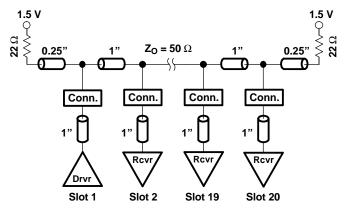


Figure 2. High-Drive Test Backplane

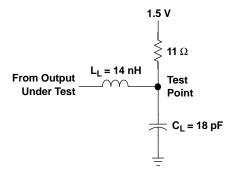


Figure 3. High-Drive RLC Network



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## **Switching Characteristics**

over recommended ranges of supply voltage and operating free-air temperature,  $V_{TT} = 1.5 \text{ V}$  and  $V_{REF} = 1 \text{ V}$  for GTLP (see Figure 3)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	EDGE RATE(1)	TYP <sup>(2)</sup>	UNIT
t <sub>PLH</sub>	A	В	Slow	5	20
t <sub>PHL</sub>	A	D	Slow	5	ns
t <sub>PLH</sub>	A	В	Fast	3.8	ns
t <sub>PHL</sub>	^	Б	i asi	3.8	113
t <sub>PLH</sub>	LEAB	В	Slow	4.9	ne
$t_PHL$	LLAD	В	Slow	4.9	ns
t <sub>PLH</sub>	LEAB	В	Fast	3.9	ns
t <sub>PHL</sub>	LLAD	В	rasi	3.9	
t <sub>PLH</sub>	CLK	В	Slow	4.8	ns
$t_PHL$	CLN	В	Slow	4.8	
t <sub>PLH</sub>	CLK	В	Fast	3.7	ns
t <sub>PHL</sub>	OLIX	Б	i asi	3.7	
t <sub>en</sub>	OEAB or OE	В	Slow	4.9	ns
t <sub>dis</sub>	OLAD OF OL	D	Olow	4.7	113
t <sub>en</sub>	OEAB or OE	В	Fast	3.5	ns
$t_{dis}$	OLAD OF OL	В	i asi	4.1	
t <sub>r</sub>	Rise time Route	outs (20% to 80%)	Slow	2	ns
ч	Nise time, b out	7413 (20 /0 10 00 /0)	Fast	1.2	113
t.	Fall time P outo	uts (80% to 20%)	Slow	2.5	ns
t <sub>f</sub>	r'all tille, b outp	uis (00 /0 i0 20 /0)	Fast	1.8	

Slow (ERC =  $V_{CC}$ ) and Fast (ERC = GND) All typical values are at  $V_{CC}$  = 3.3 V,  $T_A$  = 25°C. All values are derived from TI-SPICE models.



### PACKAGE OPTION ADDENDUM

10-Dec-2020

#### PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
SN74GTLPH1655DGGR	ACTIVE	TSSOP	DGG	64	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	GTLPH1655	Samples

(1) The marketing status values are defined as follows:

**ACTIVE:** Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead finish/Ball material Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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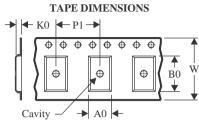
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# PACKAGE MATERIALS INFORMATION

www.ti.com 4-Oct-2022

### TAPE AND REEL INFORMATION





A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

### QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE

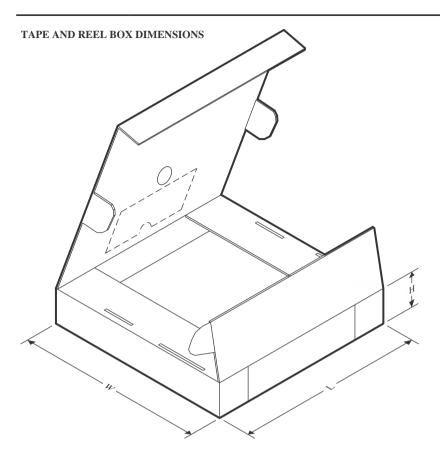


#### \*All dimensions are nominal

Device	_	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74GTLPH1655DGGR	TSSOP	DGG	64	2000	330.0	24.4	8.4	17.3	1.7	12.0	24.0	Q1

**PACKAGE MATERIALS INFORMATION** 

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### \*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74GTLPH1655DGGR	TSSOP	DGG	64	2000	367.0	367.0	45.0

### DGG (R-PDSO-G\*\*)

#### PLASTIC SMALL-OUTLINE PACKAGE

#### **48 PINS SHOWN**



NOTES: A. All linear dimensions are in millimeters.

B. This drawing is subject to change without notice.

C. Body dimensions do not include mold protrusion not to exceed 0,15.

D. Falls within JEDEC MO-153

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